40V P-Channel MOSFETs

PDP4903

General Description

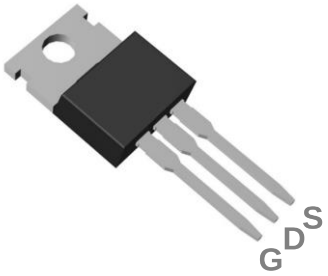
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

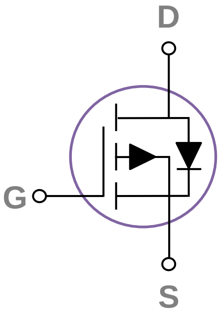
BVDSS	RDSON	ID
-40V	15mΩ	-55A

Features

- *-40V,-55A, RDS(ON) =15mΩ@VGS = -10V*
- *Fast switching*
- *Green Device Available*
- *Suit for -4.5V Gate Drive Applications*

TO220 Pin Configuration





Applications

- *MB / VGA / Vcore*
- *POL Applications*
- *Load Switch*
- *LED Application*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	-55	A
	Drain Current – Continuous (T_C=100℃)	-34	A
I_{DM}	Drain Current – Pulsed^1	-220	A
P_D	Power Dissipation (T_C=25℃)	125	W
	Power Dissipation – Derate above 25℃	1	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJC}$	Thermal Resistance Junction to Case	---	1	℃/W
$R_{θJA}$	Thermal Resistance Junction to Ambient	---	62	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-40	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-40V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-32V , V_{GS}=0V , T_J=125℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-10A	---	11.5	15	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	16	22	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.6	-2.5	V
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-10A	---	13	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2 , 3]	V_{DS}=-32V , V_{GS}=-4.5V , I_D=-10A	---	22.2	40	nC
Q_{gs}	Gate-Source Charge[2 , 3]		---	8.2	16	
Q_{gd}	Gate-Drain Charge[2 , 3]		---	8.8	16	
$T_{d(on)}$	Turn-On Delay Time[2 , 3]	V_{DD}=-20V , V_{GS}=-10V , R_G=6Ω I_D=-1A	---	23	40	ns
T_r	Rise Time[2 , 3]		---	10	20	
$T_{d(off)}$	Turn-Off Delay Time[2 , 3]		---	135	250	
T_f	Fall Time[2 , 3]		---	46	90	
C_{iss}	Input Capacitance	V_{DS}=-25V , V_{GS}=0V , F=1MHz	---	2757	4000	pF
C_{oss}	Output Capacitance		---	240	360	
C_{rss}	Reverse Transfer Capacitance		---	137	200	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	-55	A
I_{SM}	Pulsed Source Current		---	---	-110	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

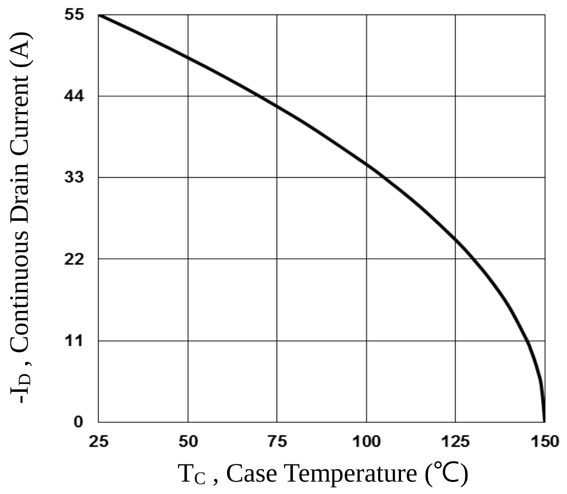


Fig.1 Continuous Drain Current vs. T_C

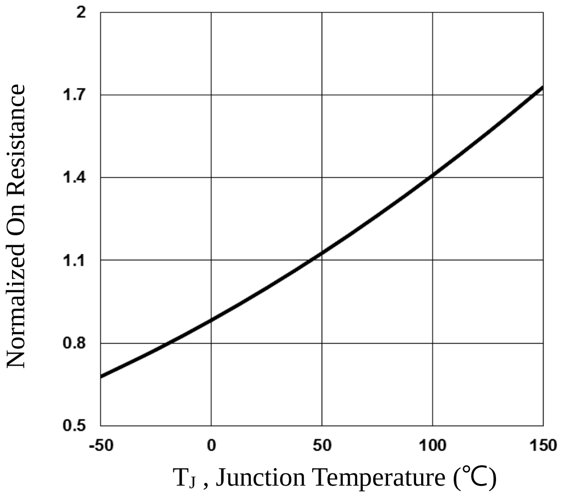


Fig.2 Normalized RDSON vs. T_J

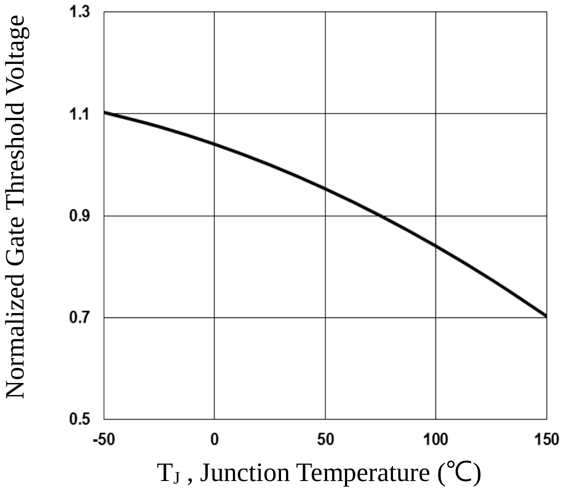


Fig.3 Normalized V_{th} vs. T_J

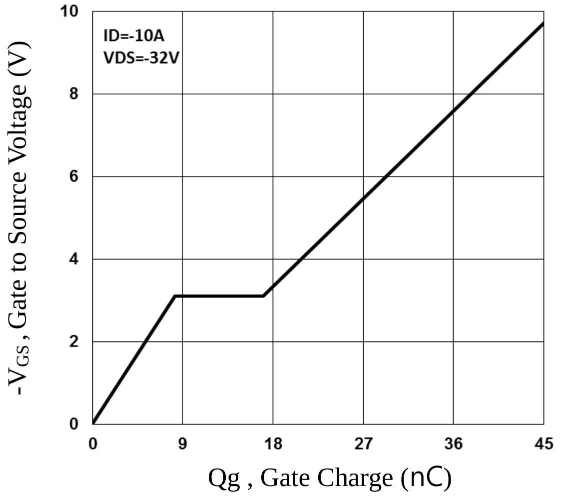


Fig.4 Gate Charge Waveform

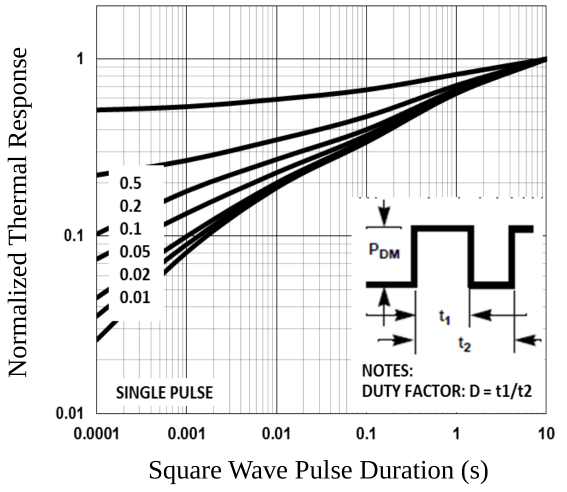


Fig.5 Normalized Transient Impedance

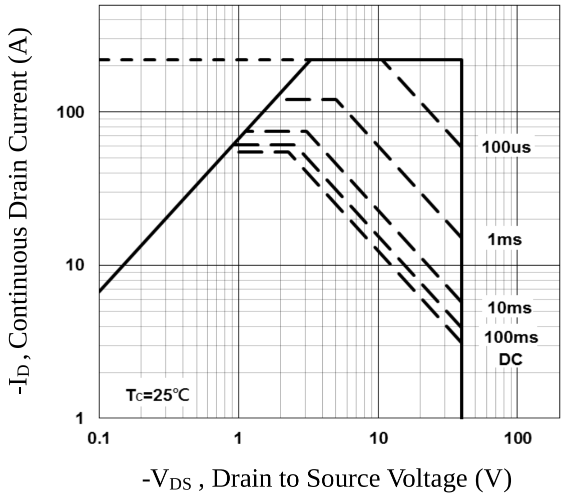


Fig.6 Maximum Safe Operation Area

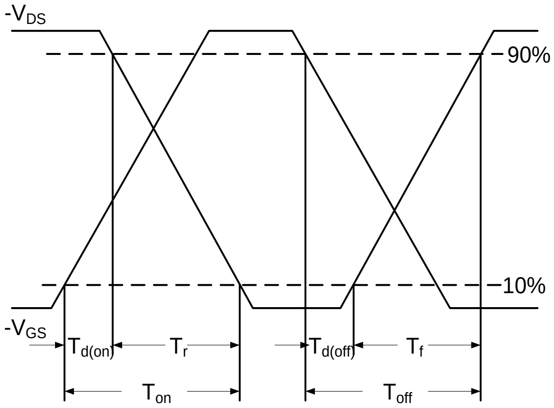


Fig.7 Switching Time Waveform

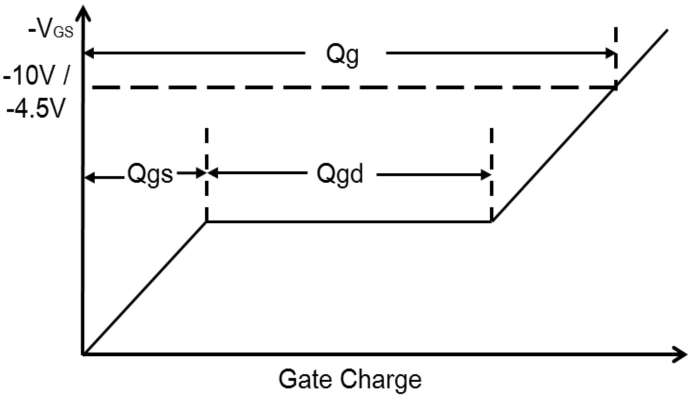
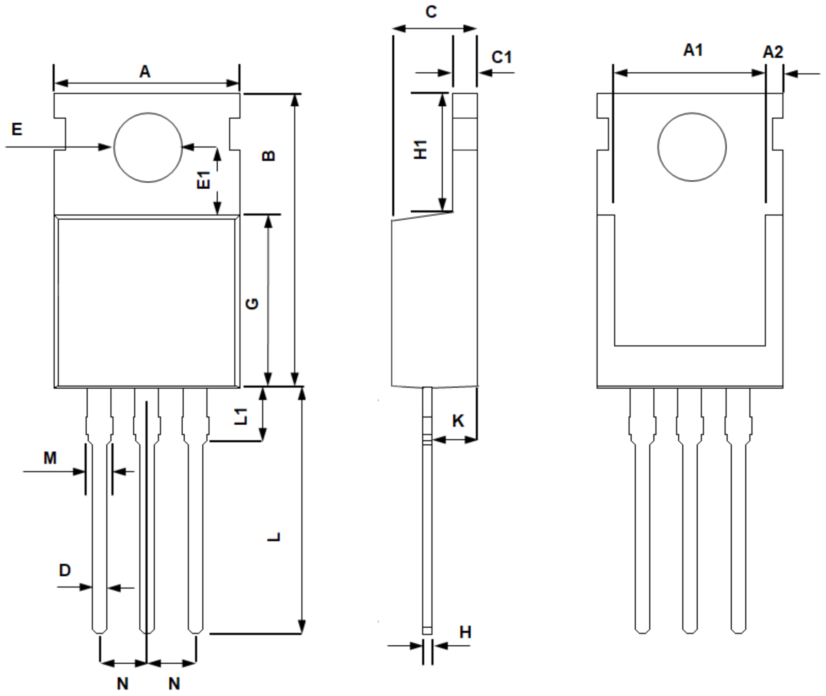


Fig.8 Gate Charge Waveform

TO220 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.400	9.700	0.409	0.382
A1	8.900	7.400	0.350	0.291
A2	1.400	0.800	0.055	0.031
B	16.500	14.500	0.650	0.571
C	4.750	4.200	0.187	0.165
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	4.000	3.300	0.157	0.130
E1	3.800	3.400	0.150	0.134
G	9.400	8.400	0.370	0.331
H	0.600	0.200	0.024	0.008
H1	6.850	6.200	0.270	0.244
K	2.850	2.100	0.112	0.083
L	14.000	12.500	0.551	0.492
L1	4.000	2.700	0.157	0.106
M	1.750	1.100	0.069	0.043
N	2.640	2.440	0.104	0.096